

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT
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Complete if Known

Application Number	10/815,312
Filing Date	April 1, 2004
First Named Inventor	Chen, Yung-Tin
Group Art Unit	1756
Examiner Name	Rosasco, Stephen John Ruggles

Attorney Docket No: MA-117

Sheet 1 of 3

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS							
Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					T ^a
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John Ruggles

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Substitute Disclosure Statement Form (PTO-1449)

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